



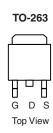
P-Channel 60-V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | |
|----------------------------------|-------------------------------------|---------------------------------|--|--|
| $V_{DS}(V)$ $r_{DS(on)}(\Omega)$ | | I _D (A) ^d | | |
| - 60 | 0.0069 at V _{GS} = - 10 V | - 110 | | |
| | 0.0088 at V _{GS} = - 4.5 V | - 110 | | |

FEATURES

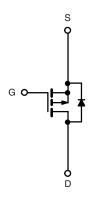
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance





Ordering Information: SUM110P06-07L

SUM110P06-07L-E3 (Lead (Pb)-free)



P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted | | | | | | |
|---|-------------------------------------|-----------------|------------------|-----|--|--|
| Parameter | Symbol | Limit | Unit | | | |
| Drain-Source Voltage | V _{DS} | - 60 | .,, | | | |
| Gate-Source Voltage | V _{GS} | ± 20 | V | | | |
| Continuous Drain Current ^d | T _C = 25 °C | C - 110 | | | | |
| $(T_J = 175 ^{\circ}C)$ | T _C = 125 °C | l _D | - 95 | A | | |
| Pulsed Drain Current | I _{DM} | - 240 | A | | | |
| Avalanche Current | L = 0.1 mH | I _{AS} | - 75 | | | |
| Single Pulse Avalanche Energy ^a | | E _{AS} | 281 | mJ | | |
| Device Directoration | T _C = 25 °C | D | 375 ^c | 14/ | | |
| Power Dissipation | T _A = 25 °C ^b | P _D | 3.75 | W | | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 175 | °C | | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------|------------------------|-------------------|---------|------|--|--|
| Parameter | | Symbol | Typical | Unit | | |
| Junction-to-Ambient | PCB Mount ^b | R _{thJA} | 40 | °C/W | | |
| Junction-to-Case | | R _{thJC} | 0.4 | C/VV | | |

Notes:

- a. Duty cycle \leq 1 %.
- b. When Mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Limited by package.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

SUM110P06-07L

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| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|----------------------|--|-------|--------|--------|------|--|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | - 60 | | | V | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | | | - 3 | 7 V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| | | V _{DS} = - 60 V, V _{GS} = 0 V | | | - 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$ | | | - 50 | μΑ | |
| | | $V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$ | | | - 250 | 1 | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$ | - 120 | | | Α | |
| | | $V_{GS} = -10 \text{ V}, I_D = -30 \text{ A}$ | | 0.0055 | 0.0069 | | |
| Drain-Source On-State Resistance ^a | r _{DO()} | $V_{GS} = -10 \text{ V}, I_D = -30 \text{ A}, T_J = 125 ^{\circ}\text{C}$ | | | 0.0115 | Ω | |
| Dialii-Source Oil-State Resistance | r _{DS(on)} | $V_{GS} = -10 \text{ V}, I_D = -30 \text{ A}, T_J = 175 ^{\circ}\text{C}$ | | | 0.0138 | | |
| | | $V_{GS} = -4.5 \text{ V}, I_D = -20 \text{ A}$ | | 0.007 | 0.0088 | | |
| Forward Transconductance ^a | g _{fs} | $V_{DS} = -15 \text{ V}, I_{D} = -50 \text{ A}$ | 20 | | | S | |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | | | 11400 | | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$ | | 1200 | | | |
| Reverse Transfer Capacitance | C _{rss} | | | 900 | | | |
| Total Gate Charge ^c | Q_g | | | 230 | 345 | | |
| Gate-Source Charge ^c | Q_{gs} | $V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -110 \text{ A}$ | | 50 | | nC | |
| Gate-Drain Charge ^c | Q_{gd} | | | 60 | | | |
| Gate Resistance | R_g | f = 1.0 MHz | | 3 | | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | 20 | 30 | | |
| Rise Time ^c | t _r | $V_{DD} = -30 \text{ V}, R_{L} = 0.27 \Omega$ | | 160 | 240 | ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | $I_D \cong$ - 110 A, V_{GEN} = - 10 V, R_g = 2.5 Ω | | 200 | 300 | 113 | |
| Fall Time ^c | t _f | | | 240 | 360 | | |
| Source-Drain Diode Ratings and Cha | aracteristics | T _C = 25 °C ^b | | | | | |
| Continuous Current | I _S | | | | - 110 | | |
| Pulsed Current | I _{SM} | | | | - 240 | Α | |
| Forward Voltage ^a | V _{SD} | I _F = - 85 A, V _{GS} = 0 V | | - 1.0 | -1.5 | V | |
| Reverse Recovery Time | t _{rr} | | | 65 | 100 | ns | |
| Peak Reverse Recovery Charge | I _{RM(REC)} | I _F = - 85 A, di/dt = 100 A/μs | | - 4.2 | - 6.3 | Α | |
| Reverse Recovery Charge | Q _{rr} | | | 0.14 | 0.32 | μС | |

Notes:

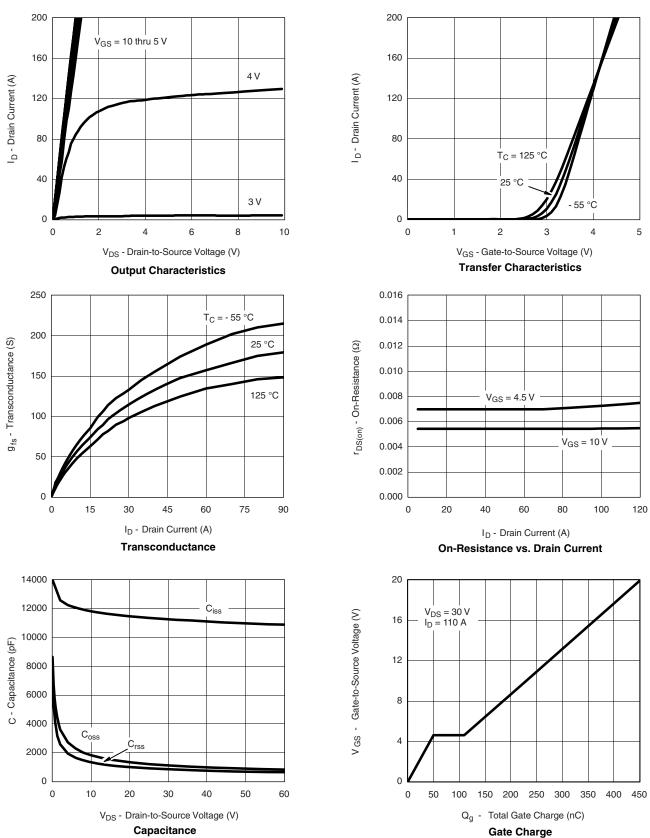
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





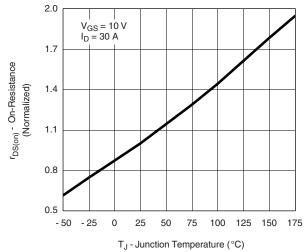
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



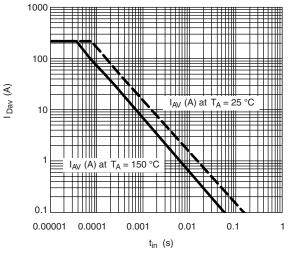
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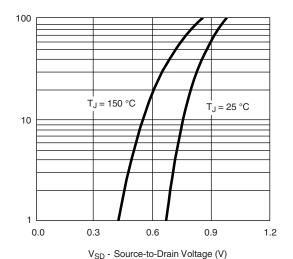
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On-Resistance vs. Junction Temperature

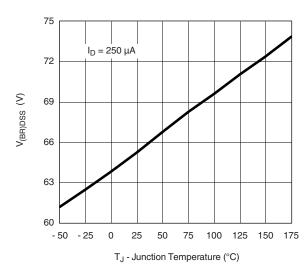


Avalanche Current vs. Time



Is - Source Current (A)

Source-Drain Diode Forward Voltage

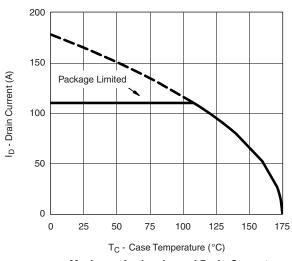


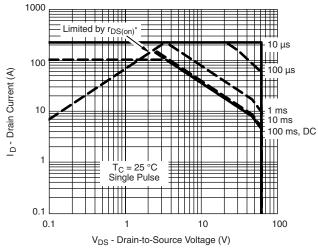
Drain Source Breakdown vs.
Junction Temperature



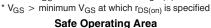


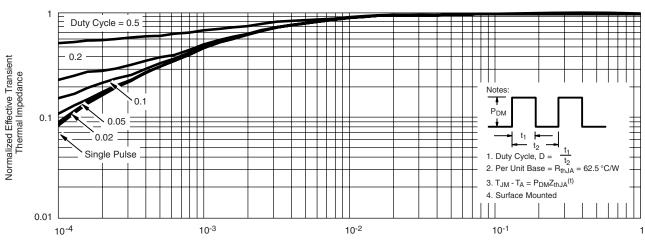
THERMAL RATINGS





Maximum Avalanche and Drain Current vs. Case Temperature





Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72439.



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



| <u> </u> | b | + + |
|----------|----------|------------|
| ≥ | | <u>, o</u> |
| 0 | ECTION A | 1 |

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

| DIM. | | INC | HES | MILLIMETERS | | |
|---------------------------------|------------|-------|-------|-------------|--------|--|
| | | MIN. | MAX. | MIN. | MAX. | |
| Α | | 0.160 | 0.190 | 4.064 | 4.826 | |
| | b | 0.020 | 0.039 | 0.508 | 0.990 | |
| | b1 | 0.020 | 0.035 | 0.508 | 0.889 | |
| | b2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| c* | Thin lead | 0.013 | 0.018 | 0.330 | 0.457 | |
| | Thick lead | 0.023 | 0.028 | 0.584 | 0.711 | |
| c1 | Thin lead | 0.013 | 0.017 | 0.330 | 0.431 | |
| CI | Thick lead | 0.023 | 0.027 | 0.584 | 0.685 | |
| | c2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| | D | 0.340 | 0.380 | 8.636 | 9.652 | |
| | D1 | 0.220 | 0.240 | 5.588 | 6.096 | |
| | D2 | 0.038 | 0.042 | 0.965 | 1.067 | |
| | D3 | 0.045 | 0.055 | 1.143 | 1.397 | |
| | D4 | 0.044 | 0.052 | 1.118 | 1.321 | |
| | Е | 0.380 | 0.410 | 9.652 | 10.414 | |
| E1 | | 0.245 | - | 6.223 | - | |
| E2 | | 0.355 | 0.375 | 9.017 | 9.525 | |
| | E3 | 0.072 | 0.078 | 1.829 | 1.981 | |
| е | | 0.100 | BSC | 2.54 BSC | | |
| K | | 0.045 | 0.055 | 1.143 | 1.397 | |
| L | | 0.575 | 0.625 | 14.605 | 15.875 | |
| L1 | | 0.090 | 0.110 | 2.286 | 2.794 | |
| L2 | | 0.040 | 0.055 | 1.016 | 1.397 | |
| L3 | | 0.050 | 0.070 | 1.270 | 1.778 | |
| L4 | | 0.010 | BSC | 0.254 BSC | | |
| | М | - | 0.002 | - | 0.050 | |
| ECN: T13-0707-Rev. K, 30-Sep-13 | | | | | | |

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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